

# **PSI3024 – Eletrônica**

**Aulas 31 e 32**

**2023**

## **CIRCUITOS INVERSORES MOS**

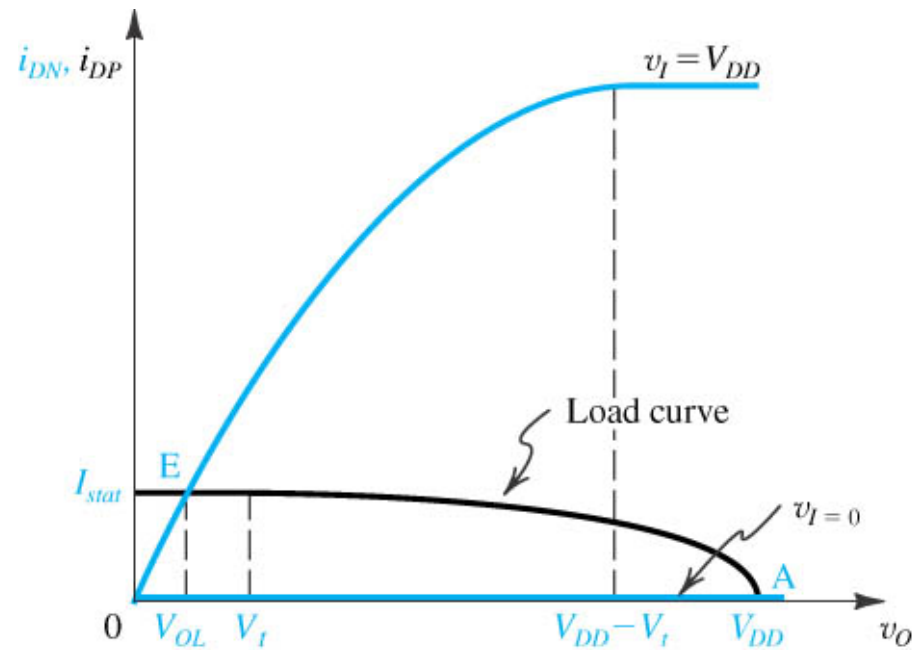
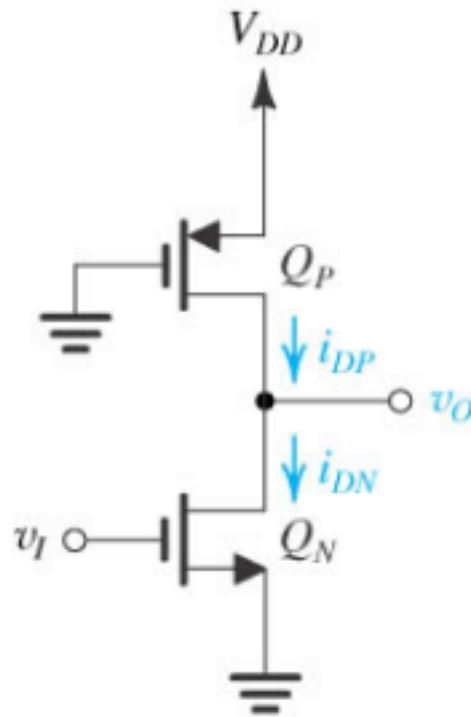
O circuito inversor é composto de dois dispositivos:

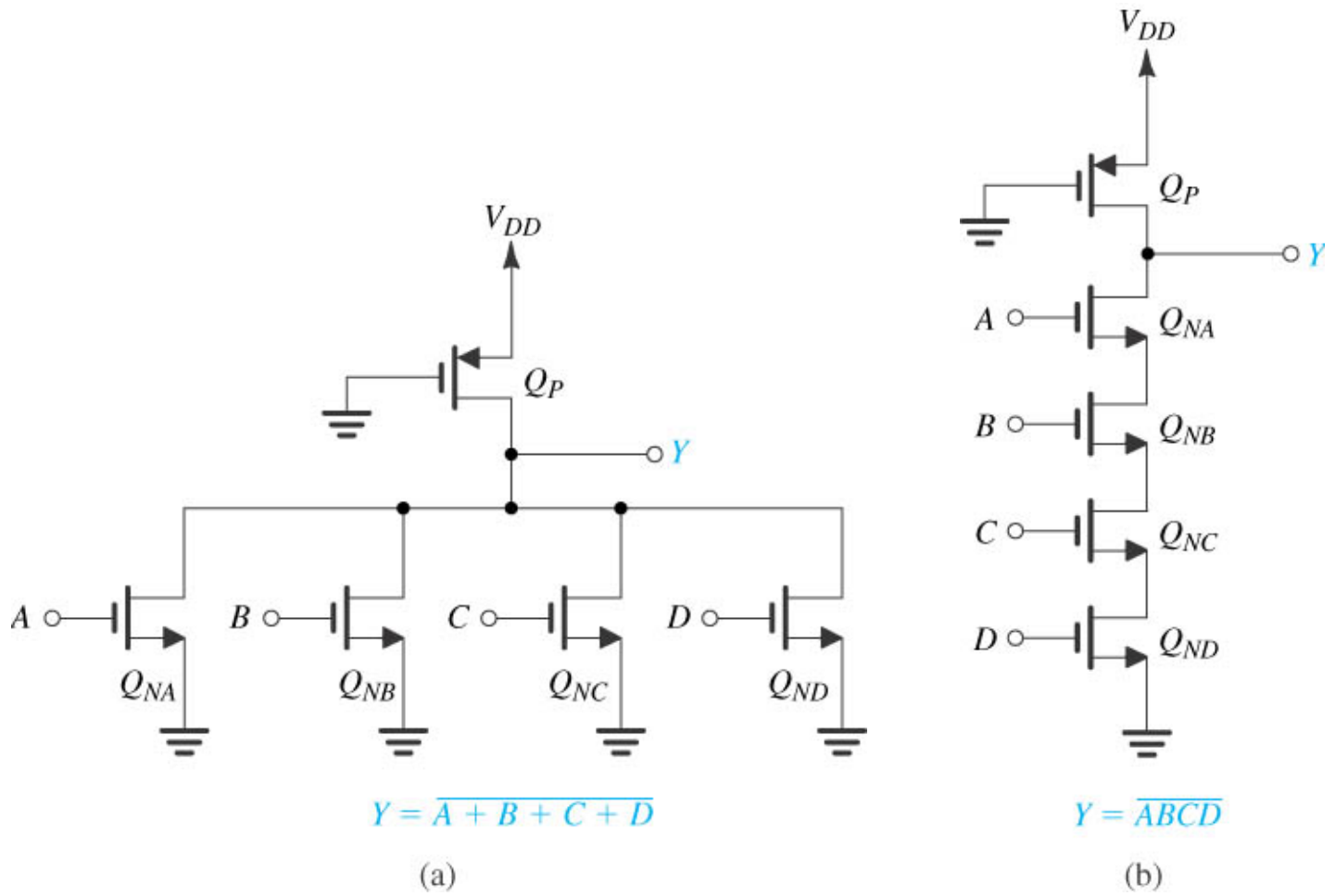
- um transistor de comando (por exemplo, nMOS)
- um elemento de carga.

O elemento de carga pode ser do tipo:

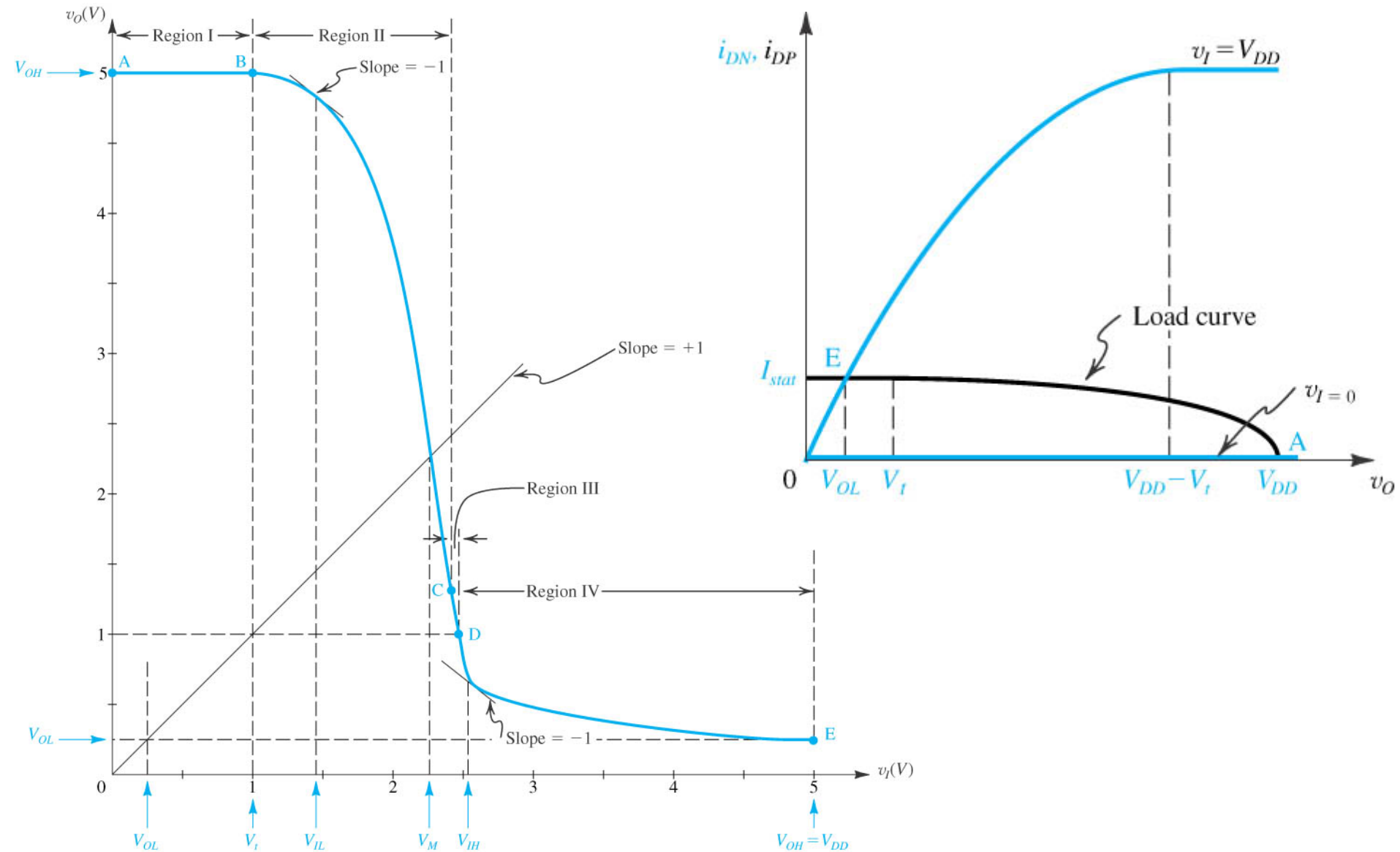
- a) resistiva
- b) transistor de enriquecimento em triodo
- c) transistor de enriquecimento em saturação
- d) transistor de depleção
- e) transistor tipo pMOS

# Inversor pseudo-NMOS





• **Figure 10.22** NOR and NAND gates of the pseudo-NMOS type.



• **Figure 10.21** VTC for the pseudo-NMOS inverter. This curve is plotted for  $V_{DD} = 5$  V,  $V_{tn} = -V_{tp} = 1$  V, and  $r = 9$ .

## Região II (segmento BC)

$$k_n = rk_p,$$

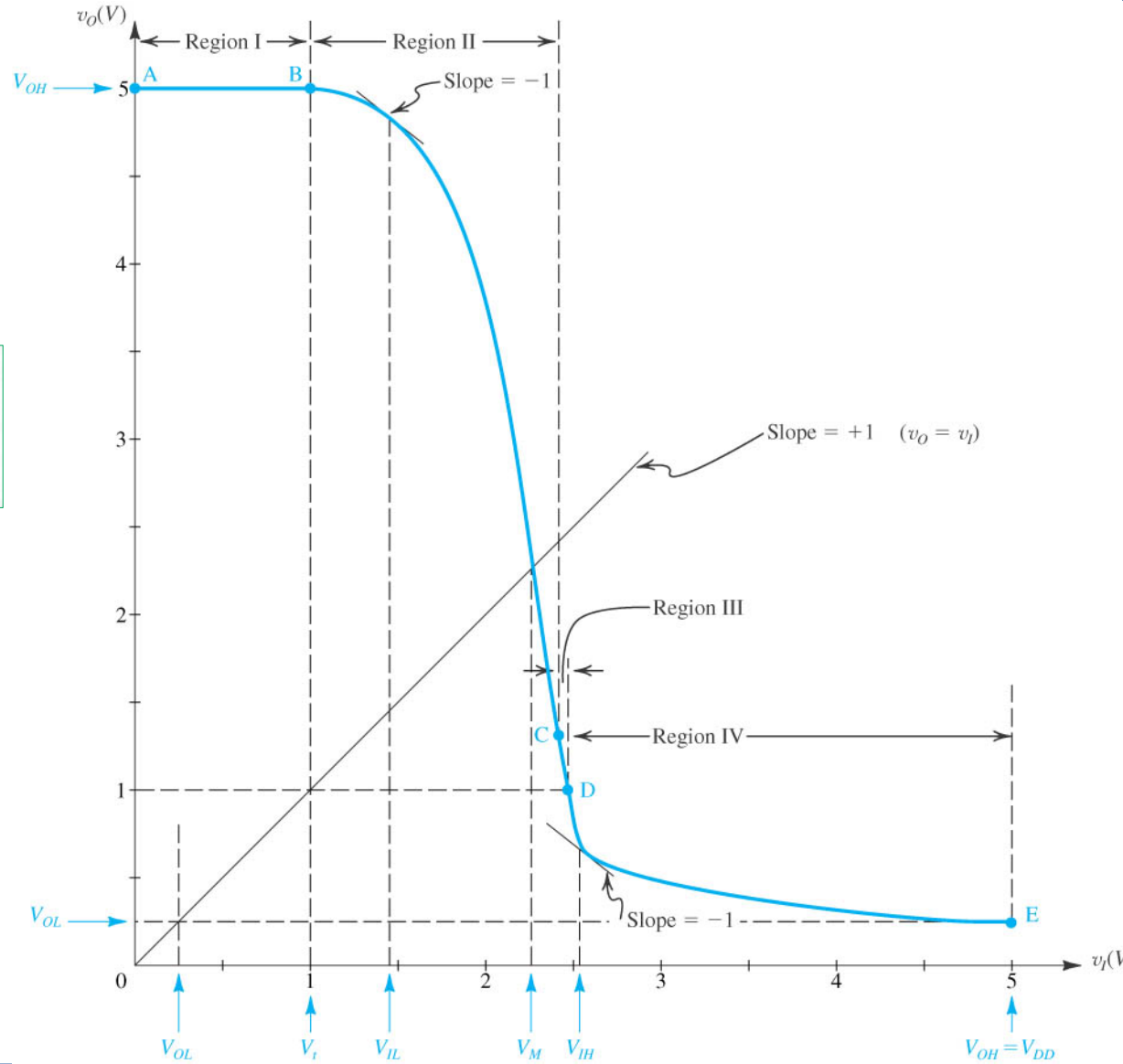
$$v_O = V_t + \sqrt{(V_{DD} - V_t)^2 - r(v_I - V_t)^2}$$

$$V_{IL} = V_t + \frac{V_{DD} - V_t}{\sqrt{r(r+1)}}$$

$$V_M = V_t + \frac{V_{DD} - V_t}{\sqrt{r+1}}$$

(ponto C)

$$v_O = v_I - V_t$$



## Região IV (segmento DE)

$$k_n = rk_p$$

## Região III (segmento CD)

ponto D  $v_O = V_t$

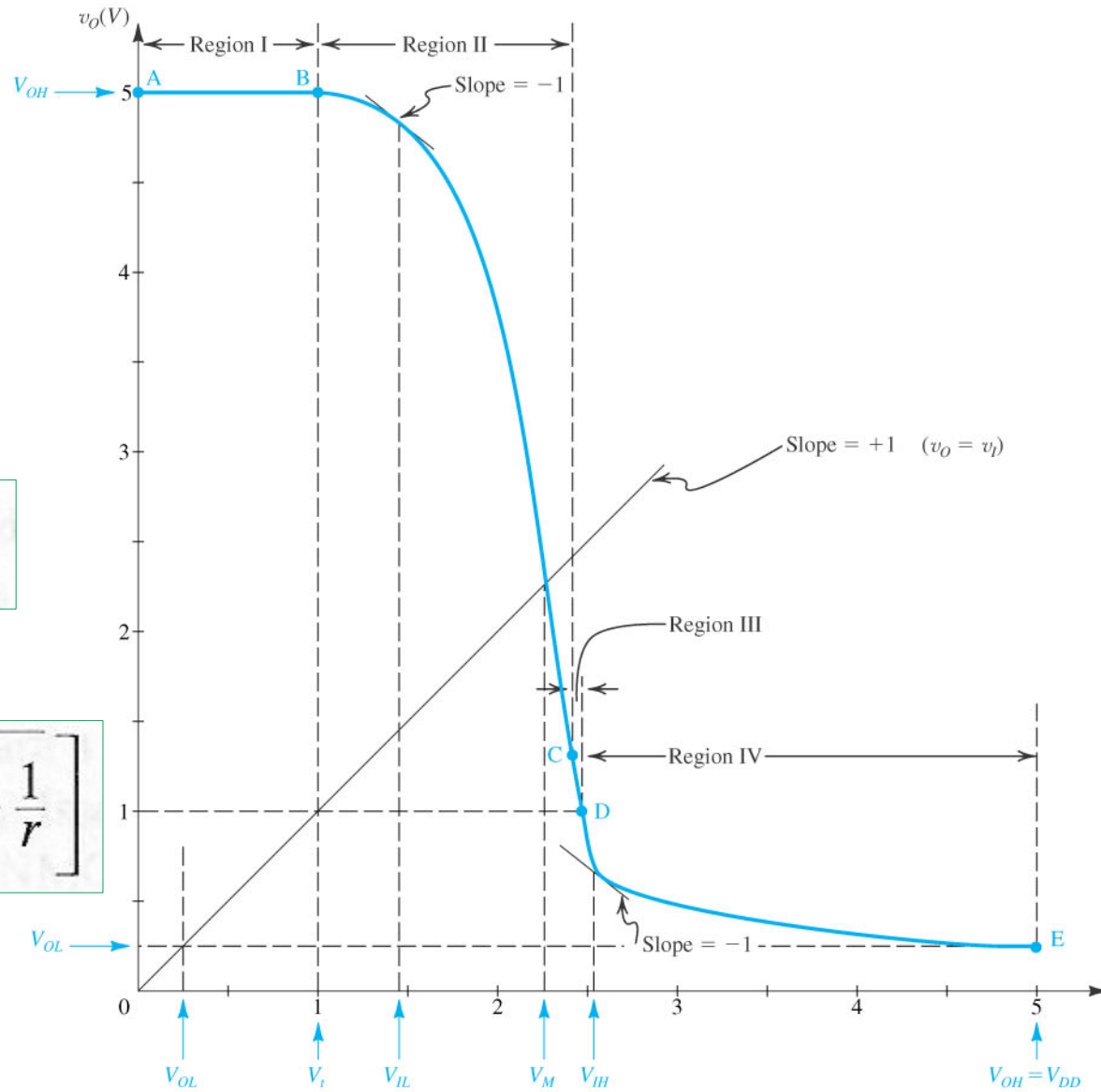
$$\partial v_O / \partial v_I = -1 \text{ e } v_I = V_{IH},$$

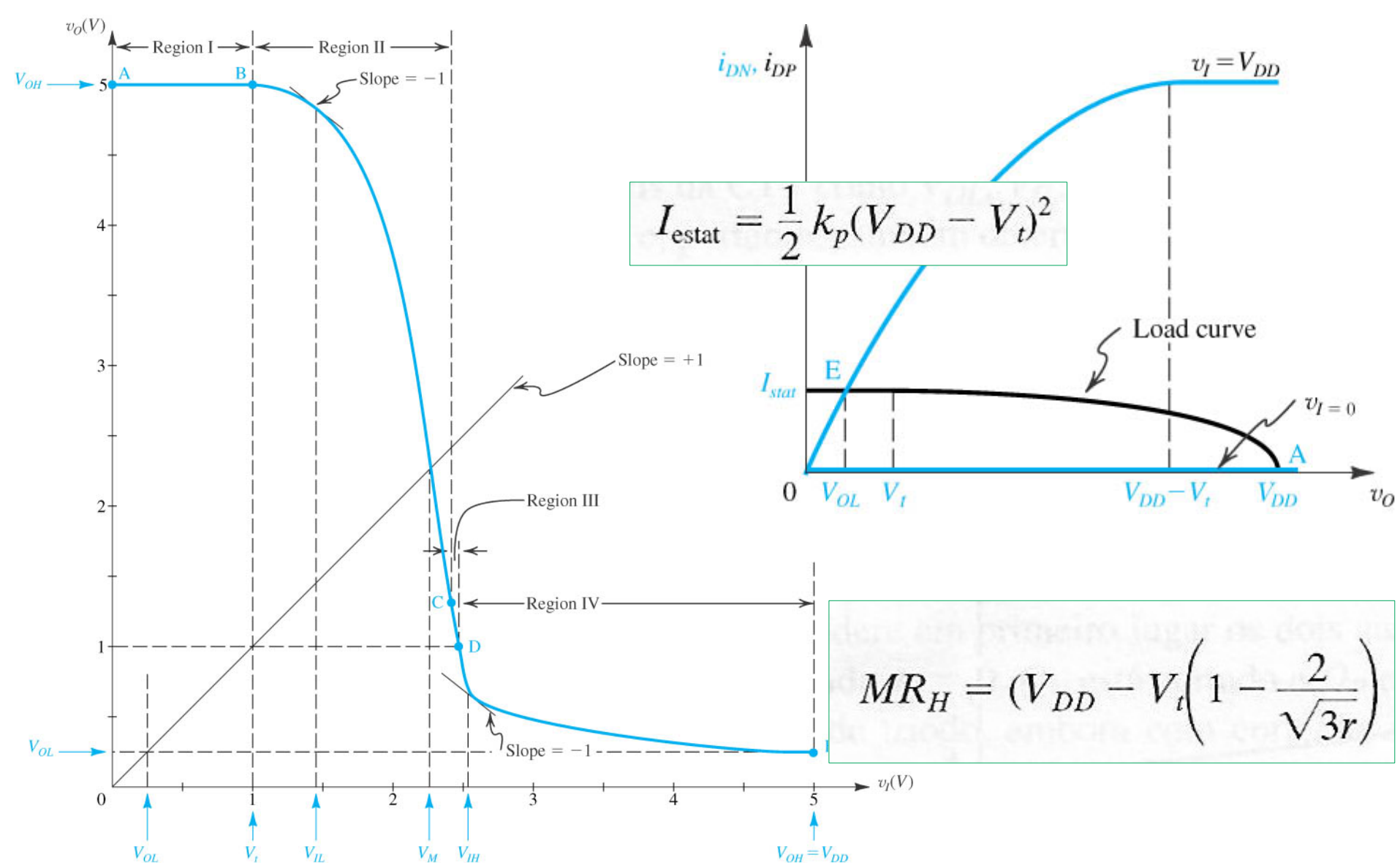
$$V_{IH} = V_t + \frac{2}{\sqrt{3}r} (V_{DD} - V_t)$$

$$v_I = V_{DD}$$

$$V_{OL} = (V_{DD} - V_t) \left[ 1 - \sqrt{1 - \frac{1}{r}} \right]$$

$$v_O = (v_I - V_t) - \sqrt{(v_I - V_t)^2 - \frac{1}{r} (V_{DD} - V_t)^2}$$





$$MR_L = V_t - (V_{DD} - V_t) \left[ 1 - \sqrt{1 - \frac{1}{r}} - \frac{1}{\sqrt{r(r+1)}} \right]$$

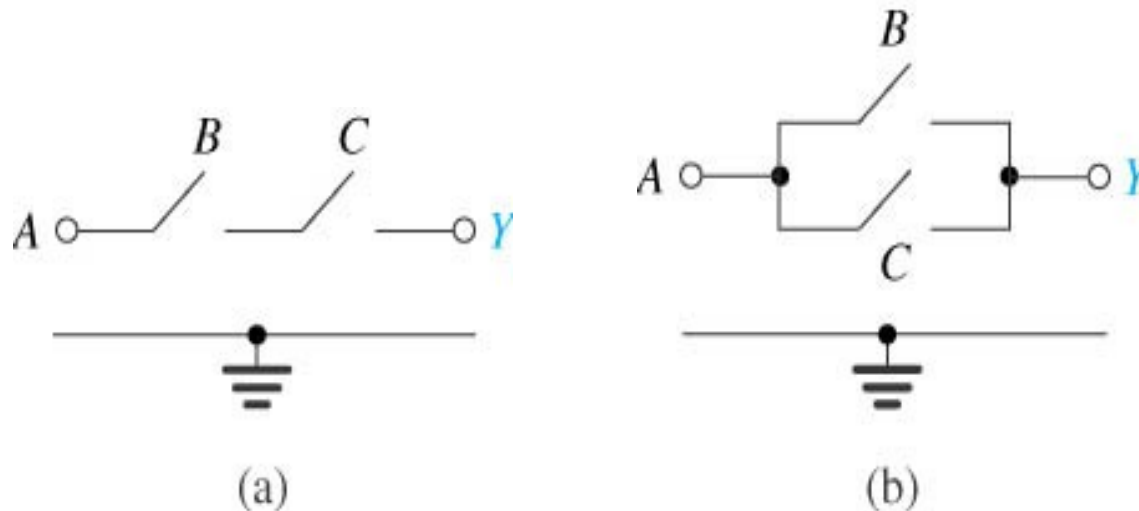


### EXEMPLO 10.3

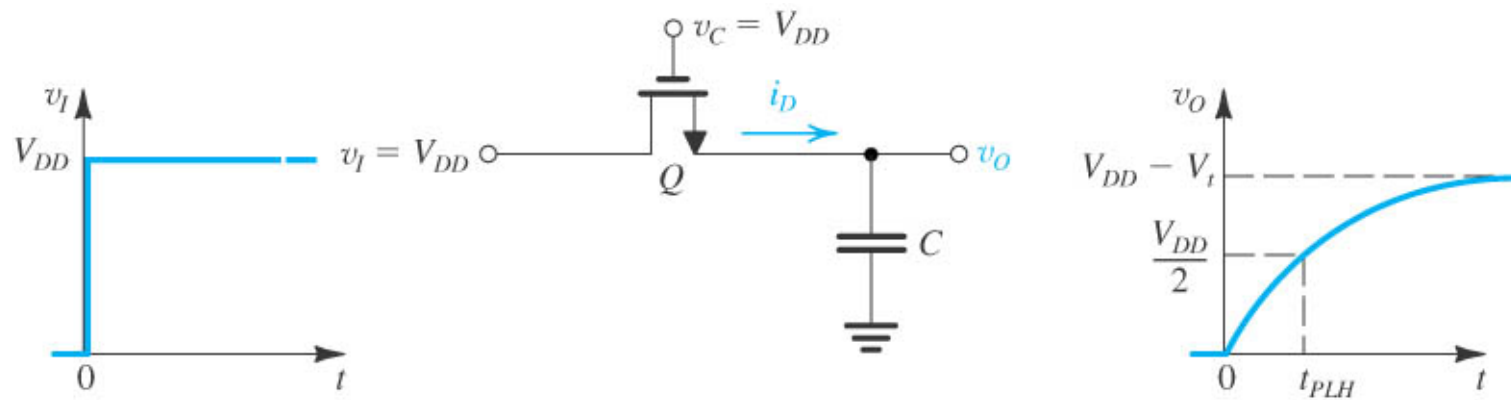
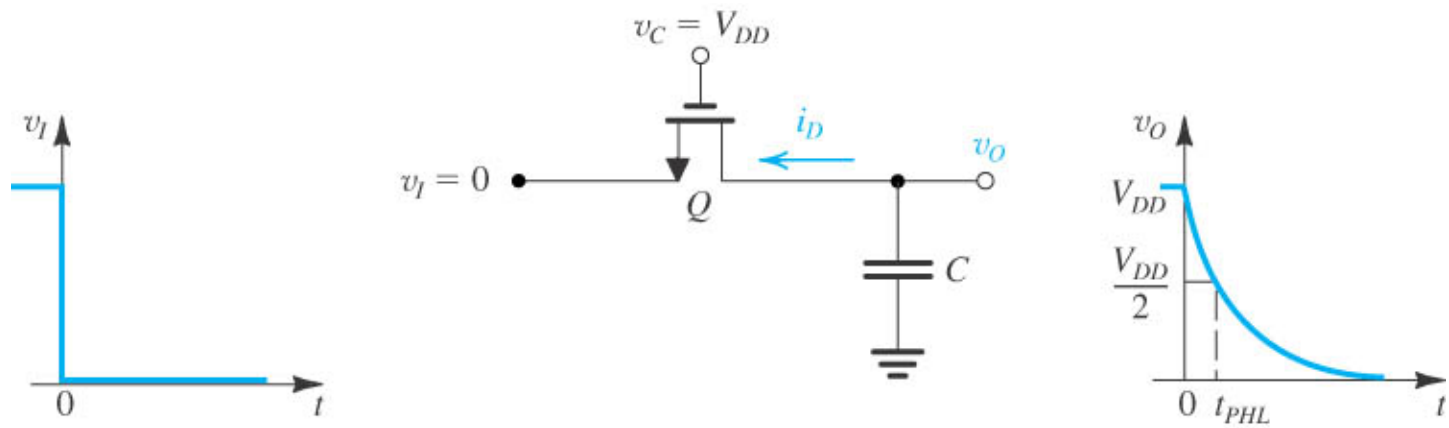
Considere o inversor pseudo-NMOS fabricado na tecnologia CMOS especificada no Exemplo 10.1, ou seja,  $\mu_n C_{ox} = 115 \mu\text{A/V}^2$ ,  $\mu_p C_{ox} = 30 \mu\text{A/V}^2$ ,  $V_{tn} = -V_{tp} = 0,4 \text{ V}$  e  $V_{DD} = 2,5 \text{ V}$ . Seja a razão  $W/L$  de  $Q_N$  de  $(0,375 \mu\text{m}/0,25 \mu\text{m})$  e  $r = 9$ . Obtenha:

- (a)  $V_{OH}$ ,  $V_{OL}$ ,  $V_{IL}$ ,  $V_{IH}$ ,  $V_M$ ,  $MR_H$  e  $MR_L$
- (b)  $(W/L)_p$
- (c)  $I_{\text{estat}}$  e  $P_D$
- (d)  $t_{PLH}$ ,  $t_{PHL}$  e  $t_p$ , supondo uma capacitância total na saída do inversor de  $7 \text{ fF}$

# Portas Lógicas com transistores de passagem

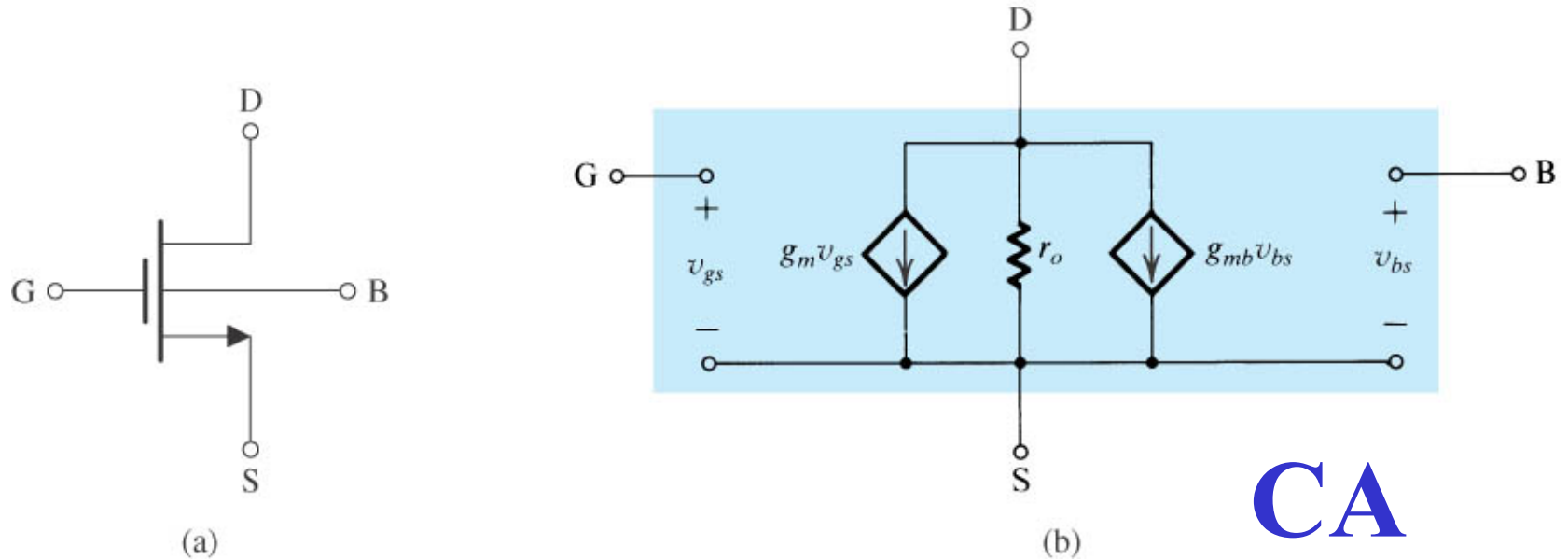


- **Figure 10.23** Conceptual pass-transistor logic gates. **(a)** Two switches, controlled by the input variables  $B$  and  $C$ , when connected in series in the path between the input node to which an input variable  $A$  is applied and the output node (with an implied load to ground) realize the function  $Y = ABC$ . **(b)** When the two switches are connected in parallel, the function realized is  $Y = A(B + C)$ .



- Figure 10.27 e 10.28 – Transistor NMOS como chave de passagem .

# Efeito de corpo

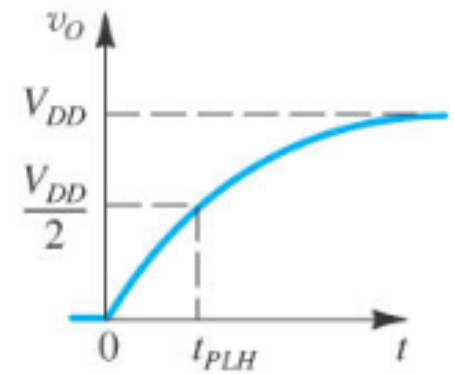
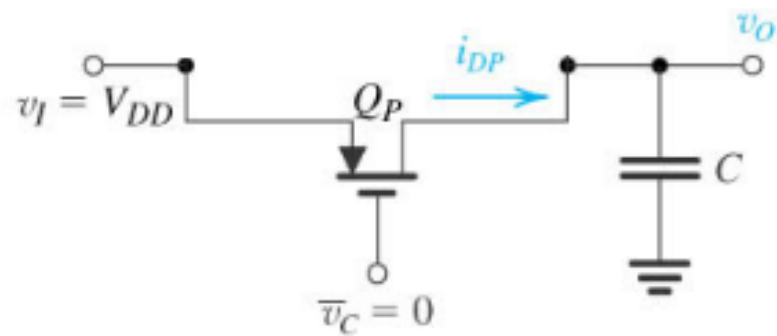
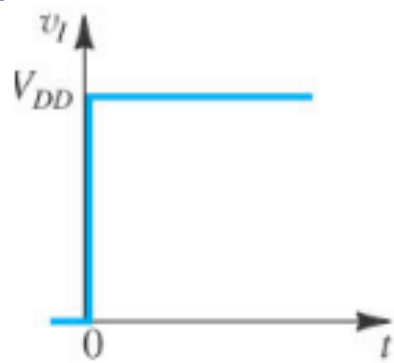


CA

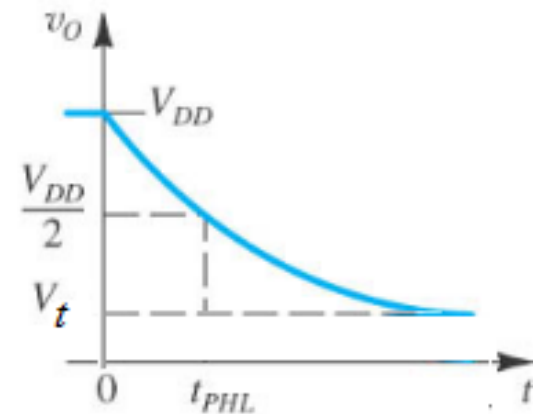
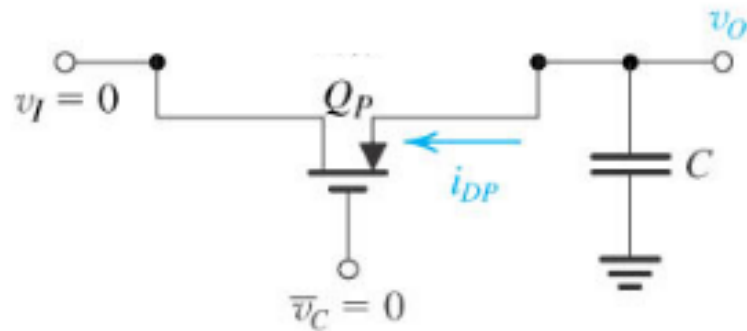
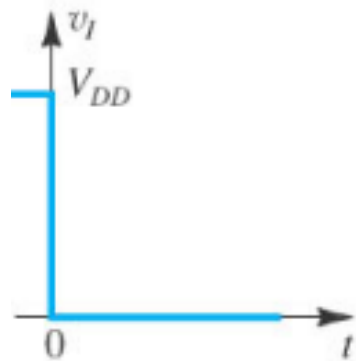
$$V_t = V_{t0} + \gamma \left( \sqrt{V_{SB} + 2 \cdot \phi_F} - \sqrt{2 \cdot \phi_F} \right)$$

CC

- **Figure 4.41** Small-signal equivalent-circuit model of a MOSFET in which the source is not connected to the body.

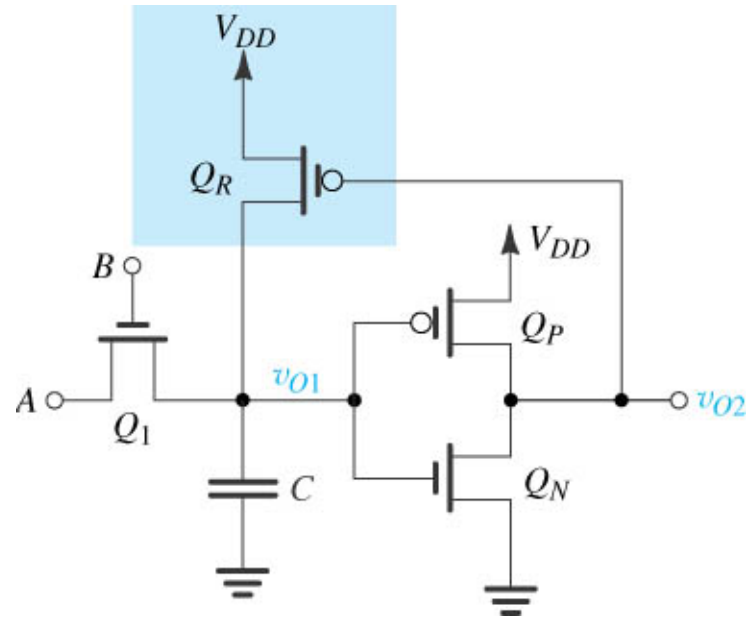


(a)

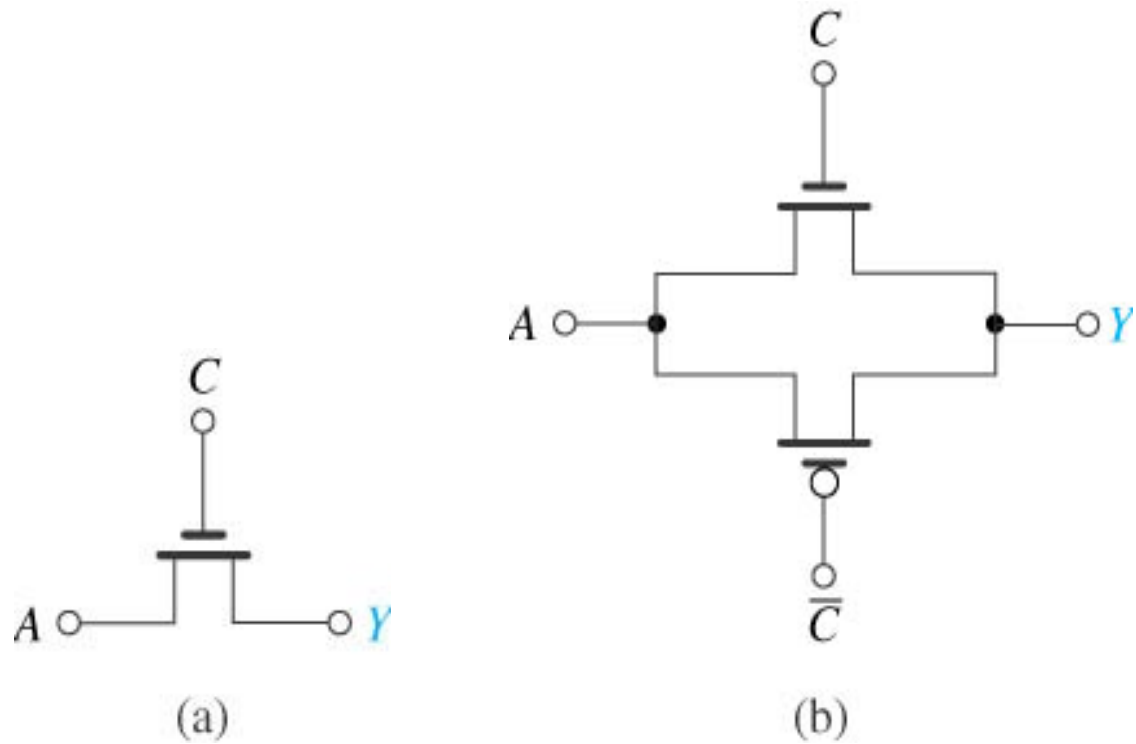


(b)

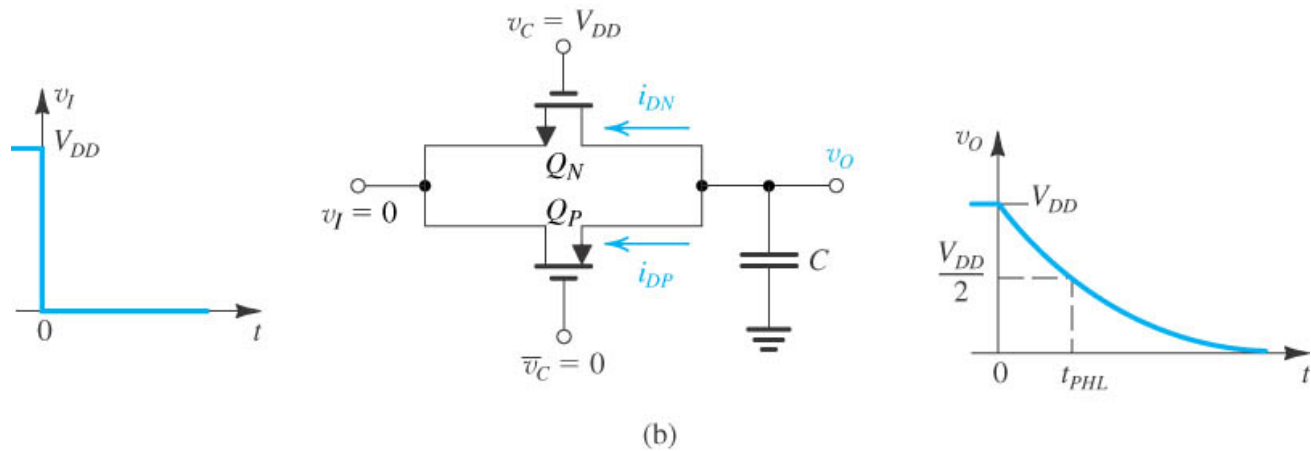
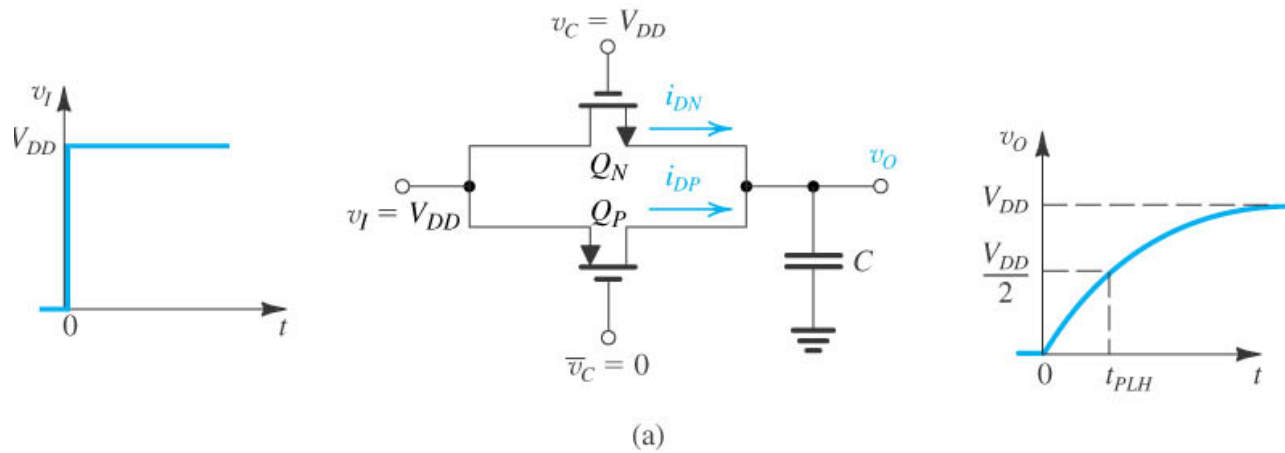
Transistor PMOS como chave de passagem .



- Figure 10.28** The use of transistor  $Q_R$ , connected in a feedback loop around the CMOS inverter, to restore the  $V_{OH}$  level, produced by  $Q_1$ , to  $V_{DD}$ .

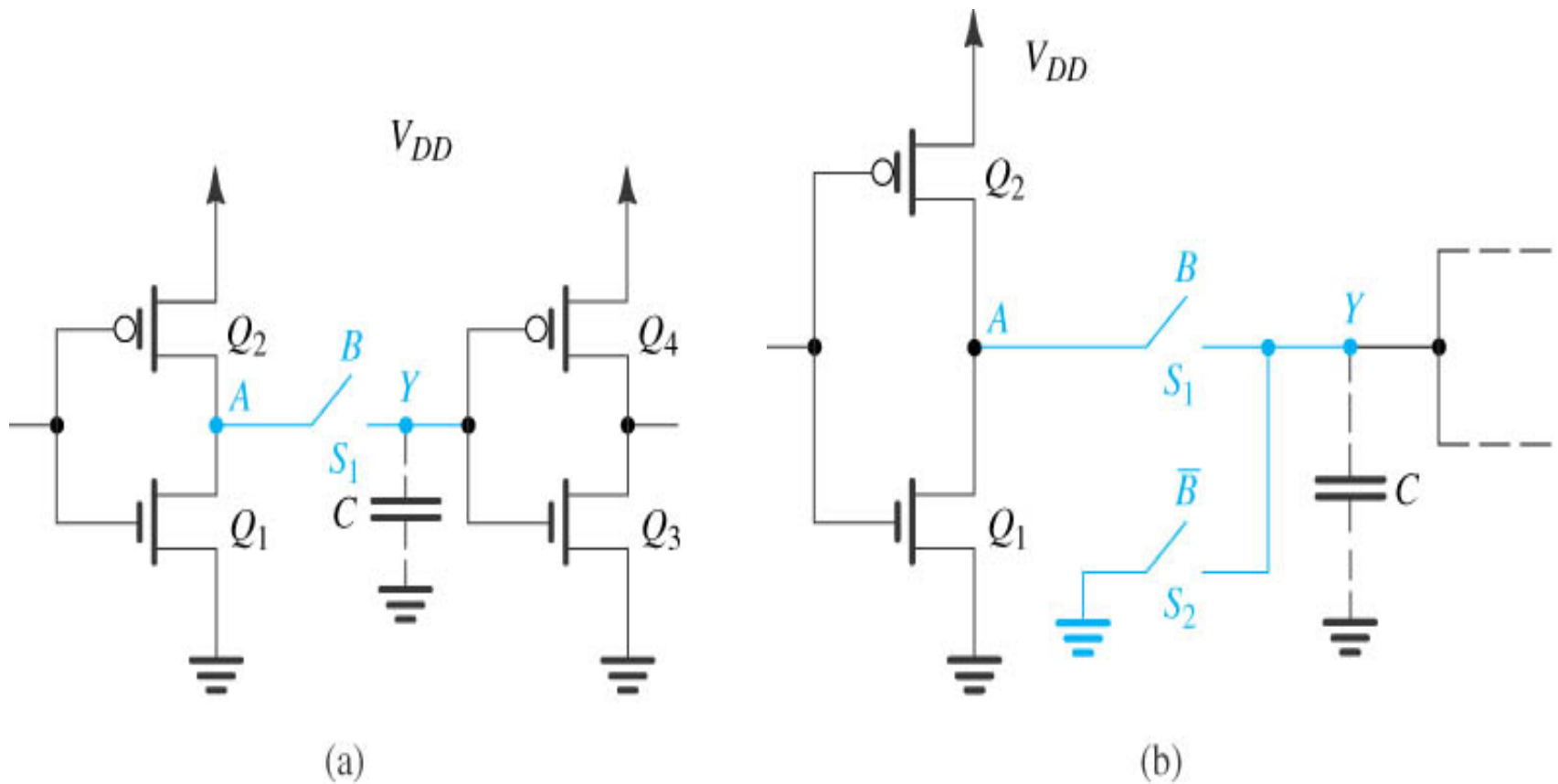


- **Figure 10.24** Two possible implementations of a voltage-controlled switch connecting nodes A and Y: **(a)** single NMOS transistor and **(b)** CMOS transmission gate.

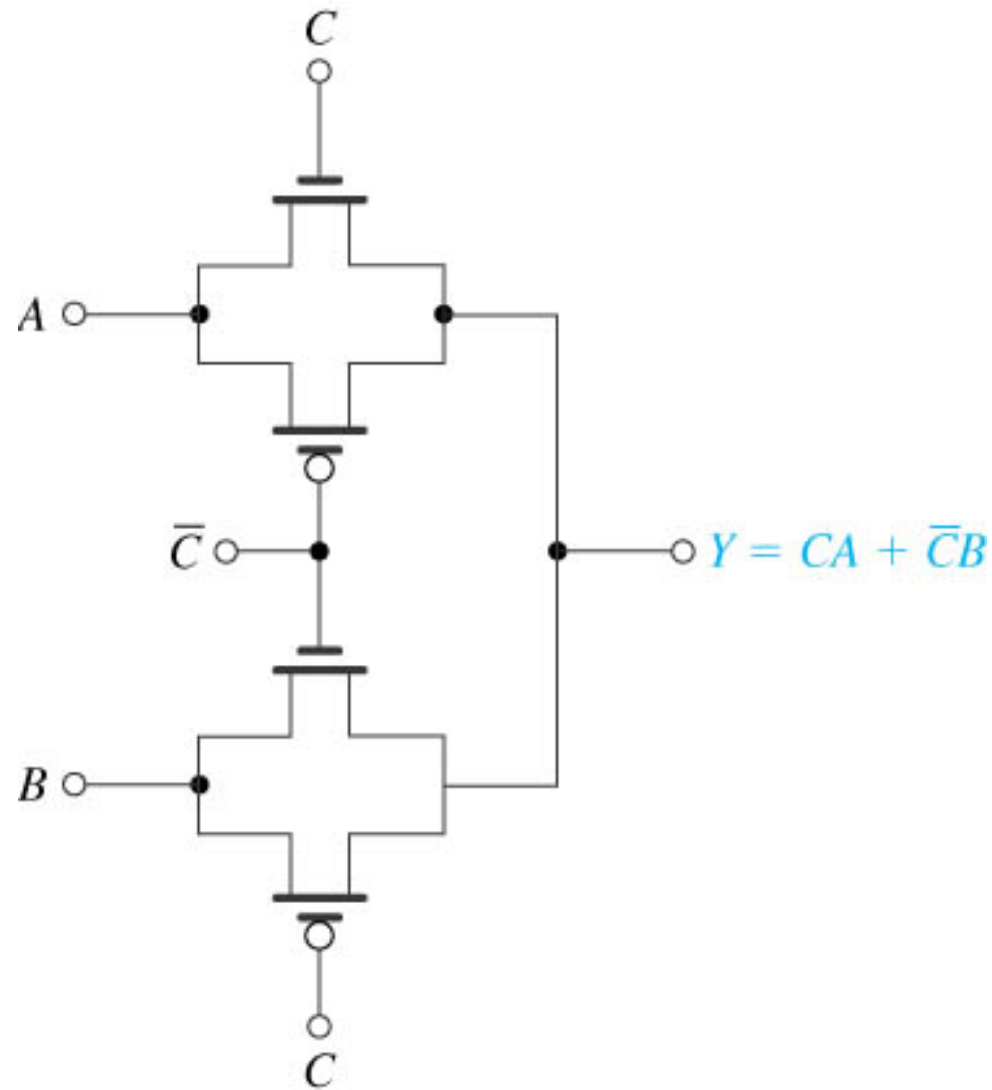


- **Figure 10.29** Operation of the transmission gate as a switch in PTL circuits with **(a)**  $v_I$  high and **(b)**  $v_I$  low.

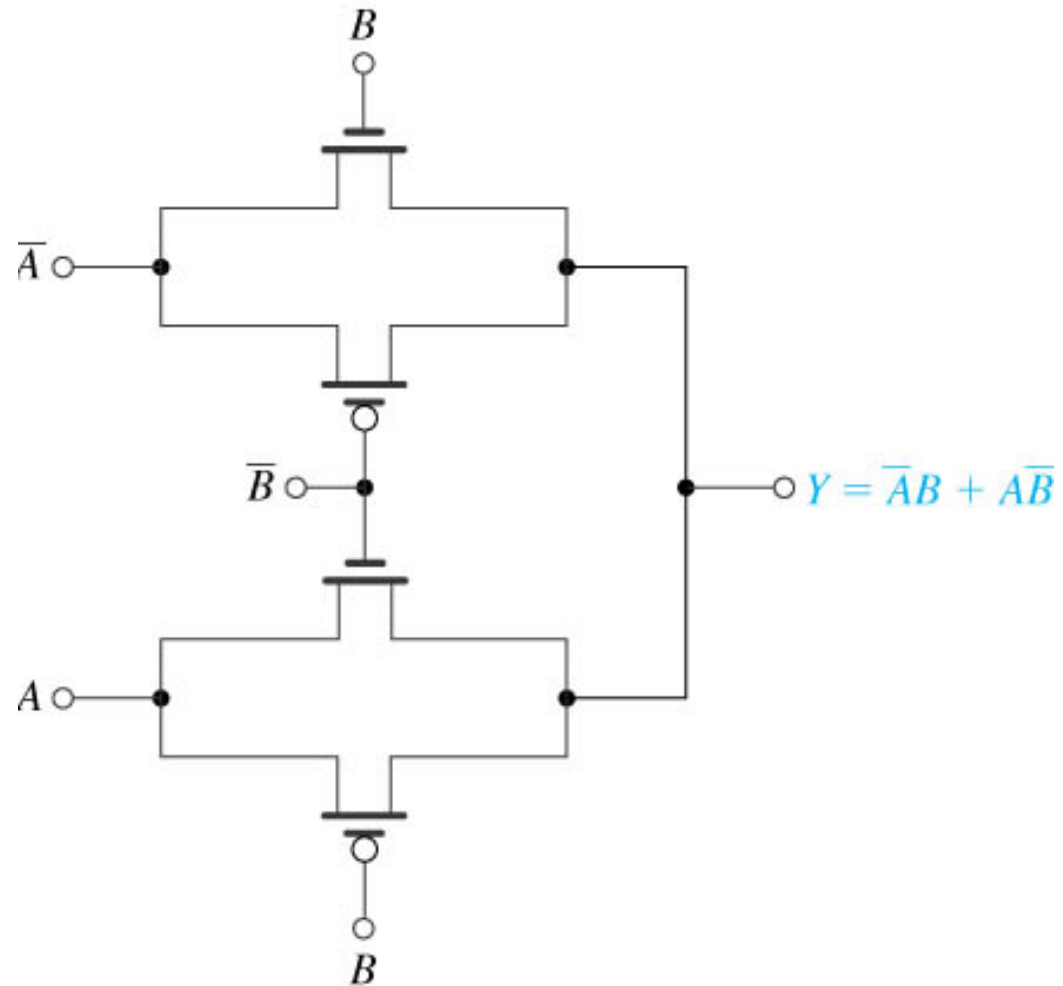




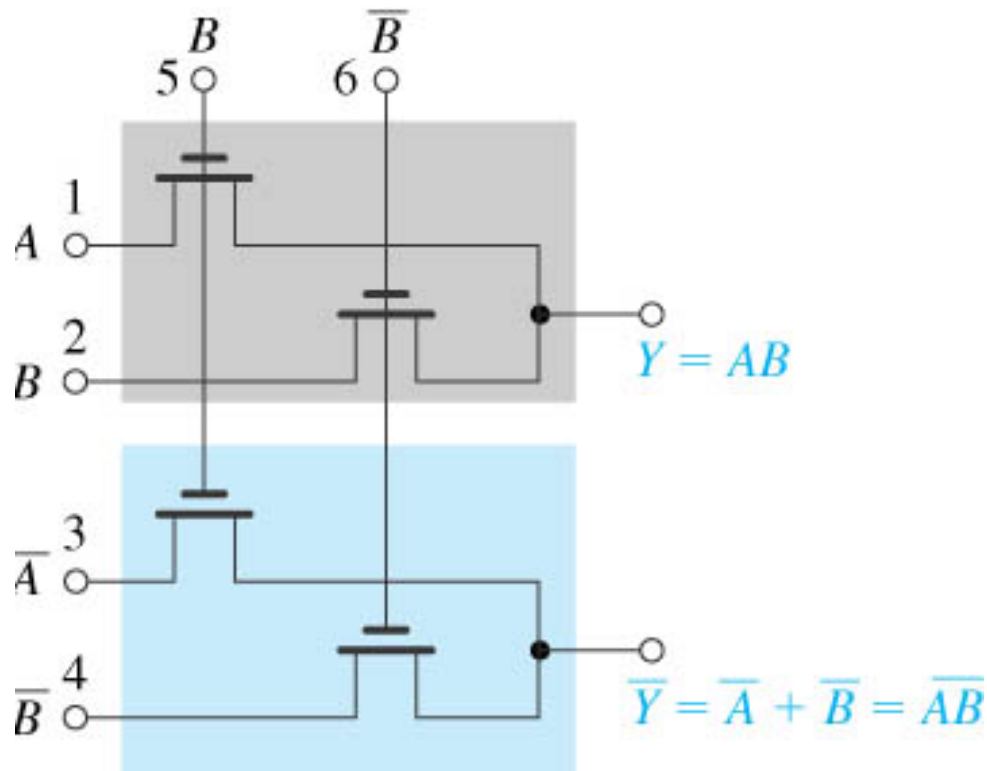
- **Figure 10.25** A basic design requirement of PTL circuits is that every node have, at all times, a low-resistance path to either ground or  $V_{DD}$ . Such a path does not exist in **(a)** when  $B$  is low and  $S_1$  is open. It is provided in **(b)** through switch  $S_2$ .



- **Figure 10.30** Realization of a two-to-one multiplexer using pass-transistor logic.



- **Figure 10.31** Realization of the XOR function using pass-transistor logic.



- Figure 10.32** An example of a pass-transistor logic gate utilizing both the input variables and their complements. This type of circuit is therefore known as complementary pass-transistor logic or CPL. Note that both the output function and its complement are generated.